

MMBT4356

PNP General Purpose Amplifier

- This device is designed for use as general purpose amplifiers and switches requiring collector currents to 500mA.
- Sourced from process 67.
- See TN4033A for characteristics.



1. Base 2. Emitter 3. Collector

Absolute Maximum Ratings * T_A=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CES}	Collector-Emitter Voltage	-80	V
V _{CBO}	Collector-Base Voltage	-80	V
V _{EBO}	Emitter-Base Voltage	-5.0	V
I _C	Collector current - Continuous	-800	mA
T _J , T _{stq}	Operating and Storate Junction Temperature Range	-55 ~ +150	°C

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired

- These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics T_A=25°C unless otherwise noted

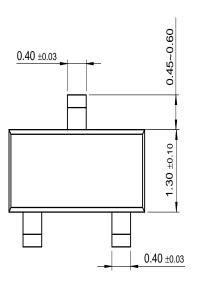
Symbol	Parameter	Max.	Units
P _D	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

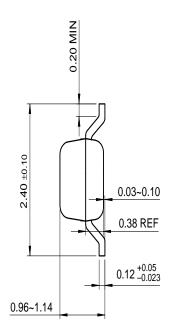
Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
Off Characte	eristics					
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage *	$I_C = -10 \text{mA}, I_B = 0$	-80			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = -10\mu A, I_E = 0$	-80			V
V _{(BR)EBS}	Emitter-Base Breakdown Voltage	$I_C = -10\mu A, I_C = 0$	-5.0			V
I _{CBO}	Collector Cutoff Current	$V_{CB} = -50V, I_{E} = 0$ $V_{CB} = -50V, I_{E} = 0, T_{A} = 75^{\circ}C$			-50 -5.0	nA μA
I _{CES}	Collector Cutoff Current	$V_{CB} = -50V, I_{E} = 0$			-50	nA
I _{EBO}	Emitter Cutoff Current	$V_{EB} = -4.0V, I_{C} = 0$			-100	μΑ
On Characte	eristics	, == -				
h _{FE}	DC Current Gain	$V_{CE} = -10V, I_{C} = -100\mu A$ $V_{CE} = -10V, I_{C} = -1.0mA$ $V_{CE} = -10V, I_{C} = -10mA$ $V_{CE} = -10V, I_{C} = -100mA$ $V_{CE} = -10V, I_{C} = -500mA$	25 40 50 40 30		250	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -150mA, I _B = -15mA I _C = -500mA, I _B = -50mA			-0.15 -0.5	V
V _{BE(on)}	Base-Emitter On Voltage	$I_C = -150 \text{mA}, I_B = -15 \text{mA}$ $I_C = -500 \text{mA}, I_B = -50 \text{mA}$			-0.9 -1.1	V V
Small Signa	I Characteristics					
C _{ob}	Output Capacitance	V _{CB} = -10V, f = 1MHz			30	pF
C _{ib}	Input Capacitance	V _{BE} = -0.5V, f = 1MHz			110	pF
h _{fe}	Small-Signal Current Gain	$V_{CE} = -10V, I_{C} = -50mA,$ f = 100MHz	1.0		5.0	
NF	Noise Figure	V_{CE} = -10V, I_{C} = -100 μ A R_{S} = 1k Ω , f = 1kHz B_{W} = 1Hz			3.0	dB
Switching C	haracteristics					
t _{on}	Turn-On Time	$V_{CC} = -30V, I_{C} = -500mA$			100	ns
t _{off}	Turn-Off Time	$I_{B1} = I_{B2} = -50 \text{mA}$			400	ns

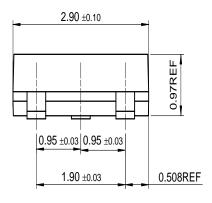
 $[\]begin{array}{c|c} \hline t_{off} & Turn\text{-}Off \ Time \\ ^* \text{Pulse Test: Pulse Width} \le 300 \mu s, \ \text{Duty} \le 2.0 \% \\ \end{array}$

Package Dimensions

SOT-23







Dimensions in Millimeters

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